

GUJARAT TECHNOLOGICAL UNIVERSITY
BE – SEMESTER – VIII. EXAMINATION – WINTER 2016

Subject Code: 180802**Date: 20/10/2016****Subject Name: VLSI Technologies****Time: 02:30 PM to 05:00 PM****Total Marks: 70****Instructions:**

1. Attempt all questions.
2. Make suitable assumptions wherever necessary.
3. Figures to the right indicate full marks.

- Q.1** (a) Why drop occurs in a MOSFET? What is threshold voltage? Derive expression of V_{th} . **07**
 (b) Explain VLSI design flow (Y- chart) in detail. **07**
- Q.2** (a) Describe CMOS fabrication (n-well) process with neat and clean diagram. **07**
 (b) Draw and explain VTC of MOS inverter. Derive expression of I_D . **07**
- OR**
- (b) Explain gradual channel approximation. Derive expression of I_D and I_D by considering channel length modulation. **07**
- Q.3** (a) Explain BIST method for chip testing. **07**
 (b) What is voltage Bootstrapping? Derive the expression of V_x . **07**
- OR**
- Q.3** (a) Explain Ad-Hoc testable technique for chip testing. **07**
 (b) What is latch-up? List and explain its causes and preventions. **07**
- Q.4** (a) Explain and derive expression for CMOS NAND2 gate. **07**
 (b) Calculate the threshold voltage V_{T0} at $V_{SB} = 0V$, for a polysilicon gate n-channel MOS transistor, with the following parameters: Substrate doping density $N_A = 10^{16} \text{ cm}^{-3}$, polysilicon gate doping density $N_D = 2 \times 10^{20} \text{ cm}^{-3}$, gate oxide thickness $t_{ox} = 500 \text{ \AA}$ and oxide-interface fixed charge density $N_{ox} = 4 \times 10^{10} \text{ cm}^{-2}$.
 Assume: $\phi_F(\text{Gate}) = 0.55V$, $n_i = 1.45 \times 10^{10} \text{ cm}^{-3}$, thermal voltage $(kT/q) = 0.026$ **07**
- OR**
- Q.4** (a) Write a detailed note on high performance Dynamic CMOS logic **07**
 (b) Consider a resistive-load inverter circuit with $V_{DD} = 5V$, $k'_n = 20 \mu A/V^2$, $V_{T0} = 0.8V$, $R_L = 200K\Omega$ and $(w/l) = 2$. Calculate the critical voltages (V_{OH} , V_{OL} , V_{IL} & V_{IH}) and find the noise margins of the circuit. **07**
- Q.5** (a) What are pass transistor circuits? Explain logic '0' and logic '1' transfer. **07**
 (b) Explain switching power dissipation of CMOS inverter. Derive power delay expression. **07**
- OR**
- Q.5** (a) What are CMOS transmission gates? Explain its region of operation. **07**
 (b) Compare and list out difference between FPGAs and CLPDs. **07**
